

Silicon NPN transistor epitaxial type DP922

[Applications]

General purpose amplifier, Switching

[Feature]

Low collector-emitter saturation voltage $V_{CE(sat)} = 1.2V$ (Max.) at $IC/IB = 3A/0.375A$

Low transition frequency $f_T = 3MHz$ (Min.) at $V_{CE} = 10V$, $IE = -0.5A$

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	100	V
Collector-emitter voltage	VCEO	100	V
Emitter-base voltage	VEBO	5	V
Collector current	IC	3	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	100	-	-	V	$IC = 100\mu A$
Collector-emitter breakdown voltage	BVCEO	100	-	-	V	$IC = 30mA$
Emitter-base breakdown voltage	BVEBO	5	-	-	V	$IE = 100\mu A$
Collector cut-off current	ICBO	-	-	1	μA	$VCB = 80V$
Collector cut-off current	ICEO	-	-	1	μA	$VCE = 80V$
Emitter cut-off current	IEBO	-	-	1	μA	$VEB = 5V$
DC current gain 1	hFE 1	20	-	-	-	$VCE = 4V, IC = 10mA$
DC current gain 2	hFE 2	25	-	-	-	$VCE = 4V, IC = 1A$
DC current gain 3	hFE 3	10	-	50	-	$VCE = 4V, IC = 3A$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	1.2	V	$IC = 3A, IB = 0.375A$
Base-emitter on voltage	VBE(on)	-	-	1.8	V	$VCE = 4V, IC = 3A$
Transition frequency	fT	3	-	-	MHz	$VCE = 10V, IE = -0.5A$

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

